

isc N-Channel MOSFET Transistor

IRFP350R

FEATURES

- Drain Current $-I_D = 16A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 400V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.3 \Omega (\text{Max})$
- Fast Switching

DESCRIPTION

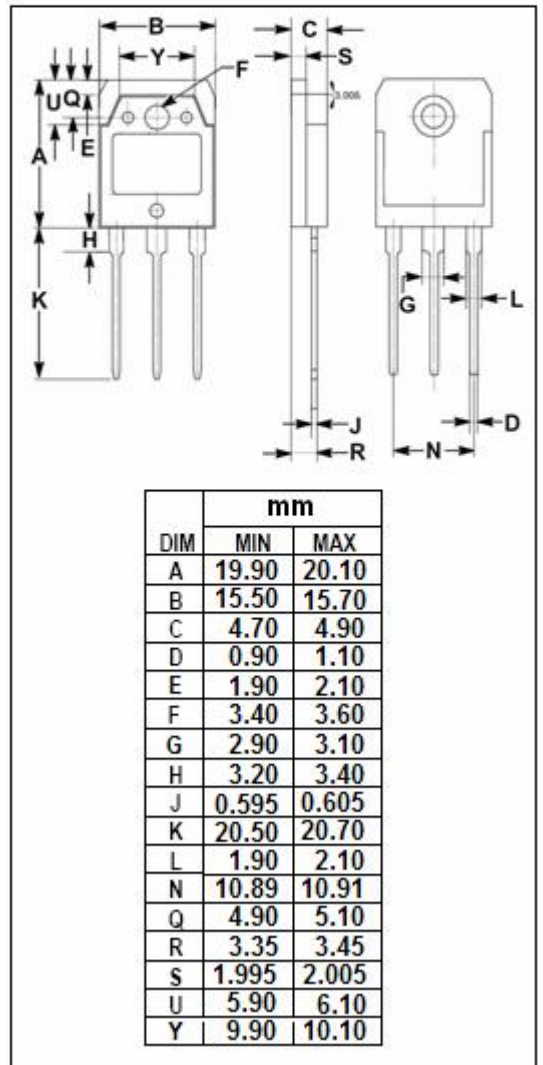
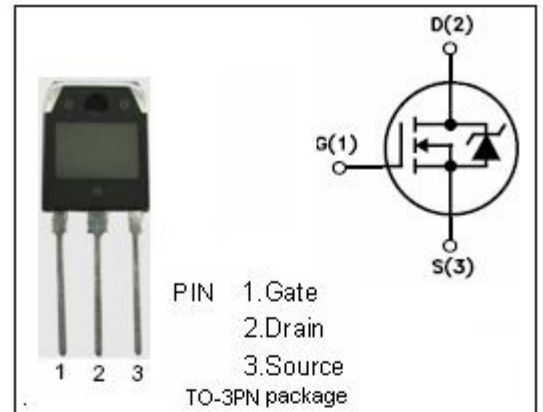
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|----------|------------|
| V_{DSS} | Drain-Source Voltage | 400 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 20 | V |
| I_D | Drain Current-Continuous | 16 | A |
| I_{DM} | Drain Current-Single Pulse | 64 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 180 | W |
| T_J | Max. Operating Junction Temperature | -55~150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|--------------|---|-----|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 0.7 | $^\circ C/W$ |
| $R_{th j-a}$ | Thermal Resistance, Junction to Ambient | 30 | $^\circ C/W$ |



isc N-Channel MOSFET Transistor**IRFP350R****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|---------------|---------------------------------|--------------------------------------|-----|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0; I_D=0.25\text{mA}$ | 400 | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}; I_D=0.25\text{mA}$ | 2 | 4 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}=10\text{V}; I_D=8.9\text{A}$ | | 0.3 | Ω |
| I_{GSS} | Gate-Body Leakage Current | $V_{GS}=\pm 20\text{V}; V_{DS}=0$ | | ± 100 | nA |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=400\text{V}; V_{GS}=0$ | | 250 | μA |
| V_{SD} | Forward On-Voltage | $I_S=16\text{A}; V_{GS}=0$ | | 1.6 | V |